

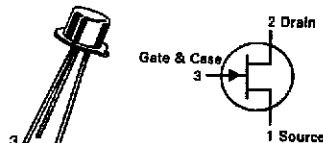
MAXIMUM RATINGS

Rating	Symbol	2N4856,A 2N4857,A 2N4858,A	2N4859,A 2N4860,A 2N4861,A	Unit
Drain-Source Voltage	V_{DS}	+40	+30	Vdc
Drain-Gate Voltage	V_{DG}	+40	+30	Vdc
Reverse Gate-Source Voltage	V_{GSR}	-40	-30	Vdc
Forward Gate Current	I_{GF}	50		mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	360 2.4		mW mW/°C
Storage Temperature Range	T_{stg}	-65 to +175		°C

2N4856, A thru 2N4861, A

2N4856, 2N4857, 2N4858
JAN, JTX, JTXV AVAILABLE

CASE 22-03, STYLE 4
TO-18 (TO-206AA)



JFET
SWITCHING

N-CHANNEL — DEPLETION

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu\text{A}$, $V_{DS} = 0$)	$V_{(BR)GSS}$	-40 -30	—	Vdc
Gate Reverse Current ($V_{GS} = -20\ \text{Vdc}$, $V_{DS} = 0$) ($V_{GS} = -15\ \text{Vdc}$, $V_{DS} = 0$) ($V_{GS} = -20\ \text{Vdc}$, $V_{DS} = 0$, $T_A = 150^\circ\text{C}$) ($V_{GS} = -15\ \text{Vdc}$, $V_{DS} = 0$, $T_A = 150^\circ\text{C}$)	I_{GSS}	— — — —	0.25 0.25 0.5 0.5	nAde μAde
Gate Source Cutoff Voltage ($V_{DS} = 15\ \text{Vdc}$, $I_D = 0.5\ \text{nAde}$)	$V_{GS(off)}$	-4.0 -2.0 -0.8	-10 -6.0 -4.0	Vdc
Drain Cutoff Current ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = -10\ \text{Vdc}$) ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = -10\ \text{Vdc}$, $T_A = 150^\circ\text{C}$)	$I_{D(off)}$	— —	0.25 0.5	nAde μAde
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current(1) ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$)	I_{DSS}	50 20 8.0	— 100 80	mAde
Drain-Source On-Voltage ($I_D = 20\ \text{mAde}$, $V_{GS} = 0$) ($I_D = 10\ \text{mAde}$, $V_{GS} = 0$) ($I_D = 5.0\ \text{mAde}$, $V_{GS} = 0$)	$V_{DS(on)}$	— — —	0.75 0.5 0.5	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Drain-Source "ON" Resistance ($V_{GS} = 0$, $I_D = 0$, $f = 1.0\ \text{kHz}$)	$r_{ds(on)}$	— — —	25 40 60	Ohms
Input Capacitance ($V_{DS} = 0$, $V_{GS} = -10\ \text{Vdc}$, $f = 1.0\ \text{MHz}$)	C_{iss}	— —	18 10	pF
Reverse Transfer Capacitance ($V_{DS} = 0$, $V_{GS} = -10\ \text{Vdc}$, $f = 1.0\ \text{MHz}$)	C_{rss}	— — —	8.0 4.0 3.5	pF

MOTOROLA SMALL-SIGNAL TRANSISTORS, FETs AND DIODES

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS (See Figure 1) (2)				
Turn-On Delay Time	$t_{d(on)}$	—	6.0	ns
Rise Time	t_r	—	3.0	ns
	t_{on}	—	4.0	ns
	t_{off}	—	10	ns
	$t_{d(off)}$	—	8.0	ns
	t_{off}	—	25	ns
Turn-Off Time	t_{off}	—	20	ns
	$t_{d(off)}$	—	50	ns
	t_{off}	—	40	ns
	$t_{d(off)}$	—	100	ns
	t_{off}	—	80	ns

(1) Pulse Test: Pulse Width = 100 ms, Duty Cycle $\leq 10\%$.(2) The $I_{D(on)}$ values are nominal; exact values vary slightly with transistor parameters.

FIGURE 1 — SWITCHING TIMES TEST CIRCUIT

